

isc Silicon NPN Power Transistor

2SC4434

DESCRIPTION

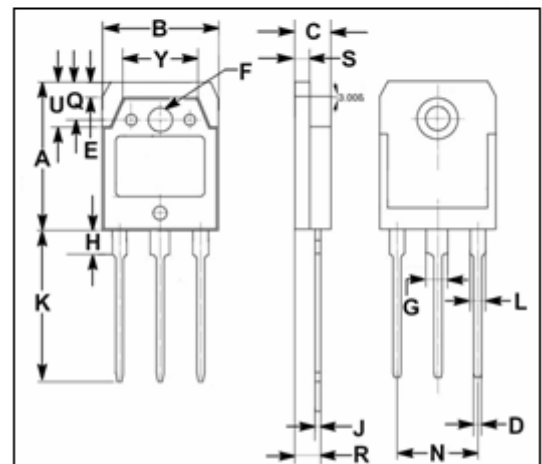
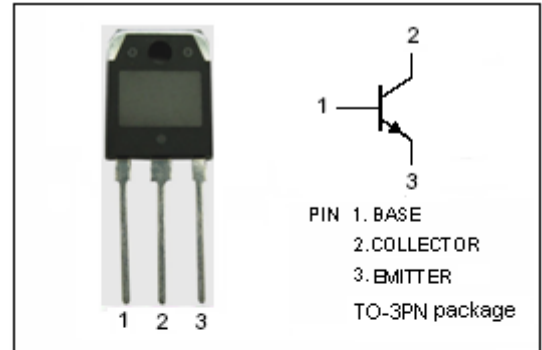
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 400V(\text{Min})$
- High Switching Speed

APPLICATIONS

- Designed for switching regulator, lighting inverter, and general purpose applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	500	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	10	V
I_C	Collector Current-Continuous	15	A
I_{CM}	Collector Current-Peak	30	A
I_B	Base Current-Continuous	5	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	120	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$



DIM	mm	
	MIN	MAX
A	19.90	20.10
B	15.38	15.42
C	4.75	4.85
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.98	3.02
H	3.20	3.40
J	0.595	0.605
K	19.95	20.25
L	1.98	2.02
N	10.89	10.91
Q	4.95	5.05
R	3.35	3.45
S	1.995	2.005
U	5.90	6.10
Y	9.90	10.10

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ELECTRICAL CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 25mA; I _B = 0	400			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 8A; I _B = 1.6A			0.7	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 8A; I _B = 1.6A			1.3	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 500V; I _E = 0			100	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 10V; I _C = 0			100	μ A
h _{FE}	DC Current Gain	I _C = 8A; V _{CE} = 4V	10		25	
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = 10V; f= 1MHz		135		pF
f _T	Current-Gain—Bandwidth Product	I _E = -1.5A; V _{CE} = 12V		10		MHz

Switching Times

t _{on}	Turn-On Time	I _C = 8A; I _{B1} = 1.6A; I _{B2} = -3.2A; V _{CC} = 200V; R _L = 25 Ω			0.5	μ s
t _{stg}	Storage Time				2.0	μ s
t _f	Fall Time				0.15	μ s